

In The Abstract

The Abstract has been amended as follows:

A linear chemical mechanical polishing apparatus that is equipped with a programmable pneumatic support platen and a method for controlling the polishing profile on a wafer surface during a linear CMP process are disclosed. The programmable pneumatic support platen is positioned juxtaposed to a bottom surface of a continuous belt for the linear CMP apparatus and positioned corresponding to a position of the wafer carrier so as to force the polishing pad against the wafer surface to be polished. The support platen has a predetermined thickness, a plurality of apertures through the thickness and a plurality of openings in a top surface in fluid communication with a gas source through the plurality of apertures.